

DUAL POWER SCHOTTKY RECTIFIERS

60A Pk, 45V

USD335C
USD345C
USD335CHR2
USD345CHR2

2

FEATURES

- Very Low Forward Voltage
- Low Recovered Charge
- Rugged Package Design (TO-3)
- High Efficiency for Low Voltage Supplies
- 45V Blocking @ Rated T_{jmax}
- 50V Repetitive Surge Voltage
- Dual Schottky Rectifier in a Single Package

ABSOLUTE MAXIMUM RATINGS (Total for USD300C Series)

Average Rectified Forward Current, I_O @ $T_C = 100^\circ\text{C}$ 30A.....

ABSOLUTE MAXIMUM RATINGS (Per Diode)

Working Peak Reverse Voltage V_{RWM} 35V 45V
 DC Blocking Voltage, V_R 35V 45V
 Peak Repetitive Surge Voltage, V_{RSM} @ I_{RM} 42V 54V
 Average Rectified Forward Current, I_O 30A in full wave configuration*
 Non-repetitive Peak
 Surge current (8.3 mS), I_{FSM} 500A
 Peak Reverse Transient Current, I_{RM} 2A
 Storage Temperature Range, T_{stg} -55°C to $+200^\circ\text{C}$
 Peak Operating Junction Temperature, T_{jmax} 175°C
 Thermal Resistance, Junction to Case, $R_{\theta JC}$ 1.4°C/W

* Each Anode Pin Limited to 18A Average.
 Package Capability 30A Average.

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^\circ\text{C}$)

Characteristic	Symbol	Limit	Units	Conditions
Maximum Instantaneous Reverse Current	i_R	10 50	mA mA	$T_C = 25^\circ\text{C}$, $V_R = V_{RWM}$ $T_C = 125^\circ\text{C}$ Pulse Width = 400 μS Duty Cycle = 1 percent
Maximum Instantaneous Forward Voltage	V_F	0.57 0.66 0.60	V V V	$i_F = 10\text{A}$, $T_C = 25^\circ\text{C}$ $i_F = 20\text{A}$, $T_C = 25^\circ\text{C}$ $i_F = 20\text{A}$, $T_C = 125^\circ\text{C}$ Pulse Width = 300 μS Duty Cycle = 1 percent
Capacitance	C_t	2000	pF	$V_R = 5.0\text{V}$
Voltage Rate of Change	dv/dt	1000	v/ μS	$V_R = V_{RWM}$

MECHANICAL SPECIFICATIONS

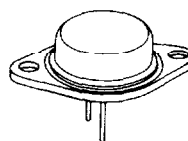
NOTE:
 Leads may be soldered to within $1/16"$ of base provided temperature-time exposure is less than 260°C for 10 seconds.

ANODE 2 ANODE 1
 CASE (CATHODE)

USD300C SERIES
 USD300CHR2 SERIES

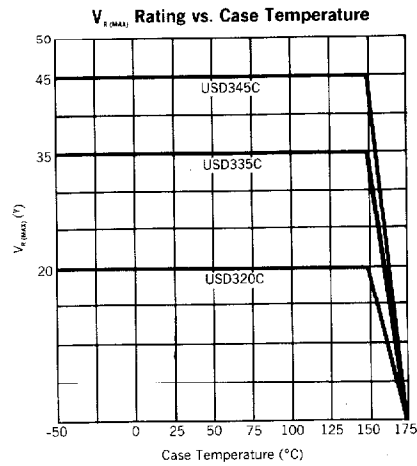
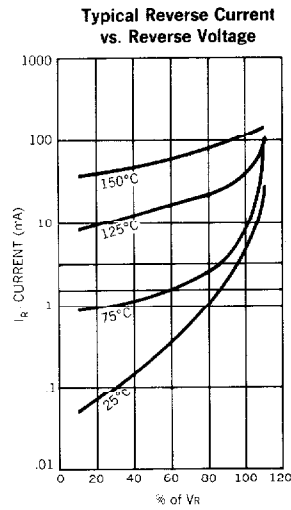
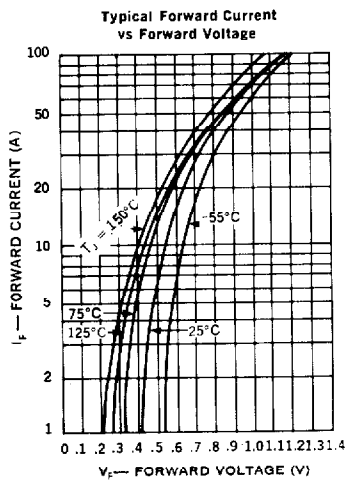
	ins.	mm.
A	.875 MAX.	22.23 MAX.
B	.135 MAX.	3.43 MAX.
C	.250-.450	6.35-11.43
D	.312 MIN.	7.92 MIN.
E	.038-.043 DIA.	0.97-1.09 DIA.
F	.188 MAX. RAD.	4.78 MAX. RAD.
G	1.177-1.197	29.90-30.40
H	.655-.675	16.64-17.15
J	.205-.225	5.21-5.72
K	.420-.440	10.67-11.18
L	.525 MAX. RAD.	13.34 MAX. RAD.
M	.151-.161 DIA.	3.84-4.09 DIA.

TO-204AA (TO-3)



Notes: All metal surfaces tin plated.

Microsemi Corp.
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 The diode experts



OPTIONAL HIGH RELIABILITY (HR2) SCREENING

The following tests are performed on 100% of the devices specified USD335CHR2, 345CHR2.

SCREEN	MIL-STD-750 METHOD	CONDITIONS
1. High Temperature	1032	2411 hours @ $T_A = 150^\circ\text{C}$
2. Temperature Cycle	1051	F, 20 Cycles, -55 to $+150^\circ\text{C}$. No dwell required @ 25°C , $t \geq 10$ min. @ extremes
3. Hermetic Seal a. Fine Leak b. Gross Leak	1071	H, Helium C, Liquid
4. Thermal Impedance		Sage Test
5. Interim Electrical Parameters	GO/NO GO	V_F and I_R @ 25°C
6. High Temperature Reverse Blocking	Similar to Method 1040	$\frac{1}{2}$ Sine Reverse, $t = 48$ Hours, $T_C = 125^\circ\text{C}$, $VRW_M = \text{rating}$, $F = 50-60$ Hz, $I_O = OA$
7. Final Electrical Parameters	GO/NO GO	$V_F + I_R$ @ 25°C PDA = 10% (Final Electricals)